Ag-Sintering of bare dies for power devices as an alternative to AuSn soldering

Ralph Schachler Chemnitzer Seminar, 13.06.2018



# Precision Matters.

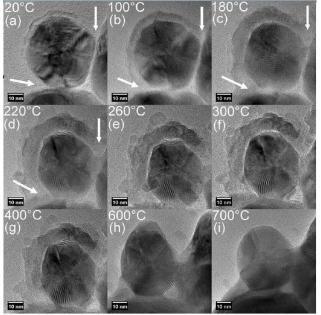


### **Prototype to Production** Flexible Solution-driven Accurate Ag-Sintering of bare dies for power devices



#### Mechanism of sintering

- Paste or foil contains micro and nano particles e.g. of silver
- High temperature and pressure starts diffusion
  - Boundaries of particles contain a lot of energy
  - Joining of particles reduces this energy (physical background)
  - The smaller the particles the easier the sintering process
- Modern sintering materials contain nano scale particles



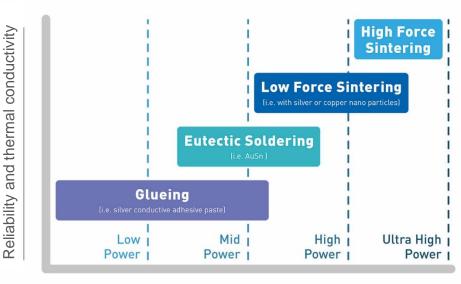
Copper Nanoparticle-Based Interconnect for 3D Heterogeneous Integration Henk v. Zeijl, ECTC 2016



#### **Demands for High Power Applications**

- High Conductivity (therm., elec.)
- High Operation Temperature
- Long Life Time
- Area of Application: Power Modules for
  - Wind Turbines
  - Solar Tower Panels
  - Electric Vehicles
  - Laser Diodes/Bars

#### **High Placement Accuracy**



Power level



#### **Properties of Ag-sintered and soldered bonds**

Material	СТЕ [10 <sup>-6</sup> /К]	Thermal Conductivity [W/mK]	Electrical Resistance [μΩcm]	Melting point [°C]	
Ag (solid)	20	429	1.6	962	
Ag (sintered)	19	100 to 300	2 to 8	962	
Au80Sn20	16	57	16	>280	
SAC305	22	55	14.5	217	

Remark: Values may vary depending on source.

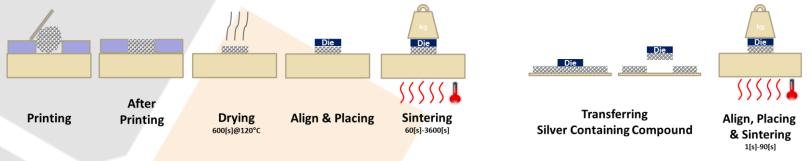
Powerful alterative!

**Standard for High Power Applications** 



#### Paste vs. foils

Paste	Foil
Low material price	No tooling (stencil) necessary
Mature technology	High performance of bond
	No post sintering necessary
	No drying and shrinking



Ag-Sintering of bare dies for power devices



#### **Typical process parameters**

	Sinter Paste	Sinter Foil	
Material	Ag		
Properties	Pasty Solid		
Compossible Material	Cu, Au, Ag		
Pre-Process Time (typ.)	≈ 600 s ≈ 10 s		
Process Time (typ.)	≈ 1 to 90 s		
Post-Process Time	up to 3600 s	n.a.	
Temperature (typ.)	≈ 200 to 300 [°C]		
Pressure (typ.)	"0" - 30 [N/mm²]	5 - 30 [N/mm²]	



#### Finetech's approach for Ag sintering for R&D and low volume

- Usual approach: Placement on diebonder and sintering in sinter press
  - Very high investment for R&D or low volume!
- FINEPLACER<sup>®</sup>s can apply high forces (e.g. up to 1000 N)
  - $\succ$  Complete sintering process on one machine  $\rightarrow$  less investment
- FINEPLACER<sup>®</sup>s reach a very high placement accuracy
  - E.g. suitable for High Power Laser Diodes

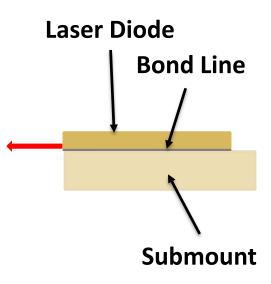






#### Foil sintering of High Power Laser Diodes

- Task: Bond laser diode on submount
  - Die size: 0.6 x 5 mm<sup>2</sup>
- Challenges:
  - Accuracy in μm range (edge to edge, not scope of these tests)
  - No pollution at facette → accurate lamination of sinter foil to chip
  - Optimal bond line condition (not in scope of these tests)
- Process parameters
  - Temperature 300°C
  - Force 90 N  $\rightarrow$  rather high force to be on the safe side
  - Time 100 s





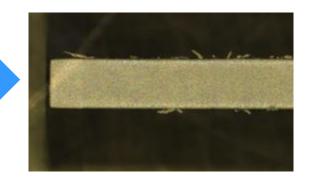
#### Foil sintering of High Power Laser Diodes



No pollution on facette:

- Foil can break and excess material is laminated to the chip
- Incomplete lamination to chip
- Solution:
  - Semi-soft support for foil improve sharpness of imprint in foil
  - Press on rubber plate to cut off excess material after lamination





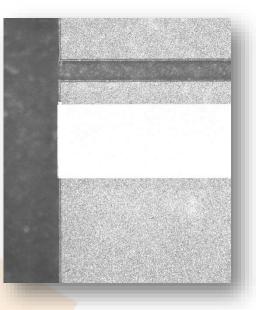


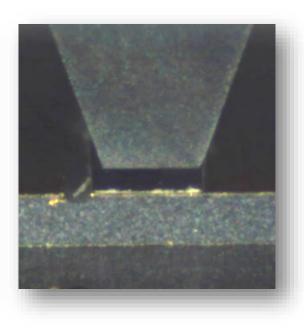
#### **Foil sintering of High Power Laser Diodes**

Results:

- Perfect alignment in µm range
- Clean facettes
- Sufficient adhesion (die breaks in shear test)

Foil sintering process successfully set up at customers!







#### Conclusion

- Ag sintering is a suitable for
  - High power application
  - High temperature applications
- Ag foil sintering is rather new, but processes have been set up successfully
- FINEPLACER<sup>®</sup>s are a good alternative for R&D and low volumes

## **Questions?**